

具有可编程固定增益的 2Vrms DirectPath™ 线路驱动器

查询样品: DRV612

特性

DirectPath™

- 消除了噼啪声/喀哒声
- 免除了输出隔直流电容器
- 3V 至 3.6V 电源电压
- 低噪声及THD
 - SNR > 105dB (在—1x 增益条件下)
 - 典型 Vn < 12μVms (在 20Hz 至 20kHz 频率 范围内和
 - -1x 增益条件下)
 - THD + N < 0.003% (在 10kΩ 负载和 —1x 增益条件下)
- 可为 600Ω 负载提供 2Vrms 输出电压
- 单端输入和输出
- 可编程增益选择减少了组件的数量
 - 13x 增益值
- 具有大于 80 dB 衰减的有源静音
- 具短路和热保护功能
- ±8 kV HBM ESD 保护输出

应用

- PDP / LCD TV
- DVD 播放机
- 迷你型/微型组合音响系统
- 声卡

说明

DRV612 是一款单端、2Vrms 立体声线路驱动器,专为缩减组件数量、板级空间和成本而设计。 对于那些将尺寸和成本作为关键设计参数的单电源电子产品而言,该器件是理想的选择。

ZHCS317B - DECEMBER 2010 - REVISED APRIL 2011

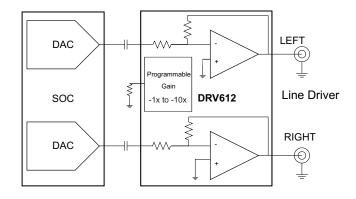
DRV612 既不需要采用一个高于 3.3V 的电源来产生其 5.6V_{DD} 输出,也不需要一个分离轨电源。

DRV612 的设计运用了 TI 的 DirectPath 专利技术,集成了一个充电泵以产生一个负电源轨,可提供一个干净、无噼啪声的接地偏置输出。 DRV612 能够向一个600Ω 负载输送 2Vrms 驱动电压。 另外,DirectPath技术还允许去除昂贵的输出隔直流电容器。

该器件具有固定增益单端输入和一个增益选择引脚。 通过在该引脚上使用单个电阻器,设计人员就能够从 13 种内部可编程增益设定值中进行选择,以使线路驱 动器与编解码器输出电平相匹配。 另外,它还削减了 组件数量和板级空间。

线路输出具有 ±8 kV HBM ESD 保护等级,从而实现了简单的 ESD 保护电路。 DRV612 内置了具有大于 80 dB 衰减的有源静音控制功能电路,用于实现无噼啪声的静音接通/关断控制。

DRV612 采用 14 引脚 TSSOP 封装和 16 引脚 QFN 封装。 如需一款具有兼容焊脚的立体声头戴式耳机驱 动器,请查阅 TPA6139A2 的文档资料 (SLOS700)。



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Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.





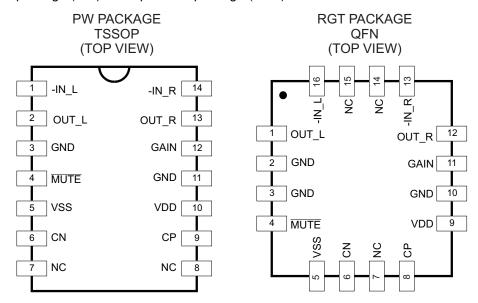
These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

GENERAL INFORMATION

TERMINAL ASSIGNMENT

The DRV612 is available in package:

• 14-pin TSSOP package (PW) or 16-pin QFN package (RGT)



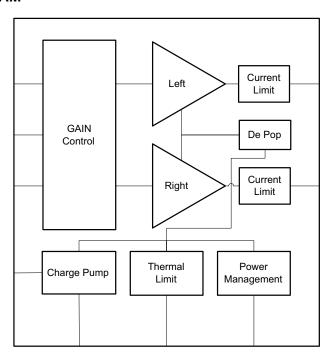
PIN FUNCTIONS

	PIN		FUNCTION ⁽¹⁾	DESCRIPTION
NAME	PW NO.	RGT NO.		
-IN_L	1	16	I	Negative input, left channel
OUT_L	2	1	0	Output, left channel
GND	3, 11	2, 3, 10	Р	Ground
MUTE	4	4	1	MUTE, active low
VSS	5	5	0	Change Pump negative supply voltage
CN	6	6	I/O	Charge Pump flying capacitor negative connection
NC	7, 8	7. 14, 15		No internal connection
СР	9	8	I/O	Charge Pump flying capacitor positive connection
VDD	10	9	Р	Supply voltage, connect to positive supply
GAIN	12	11	I	Gain set programming pin; connect a resistor to ground. See 表 1 for recommended resistor values
OUT_R	13	12	0	Output, right channel
-IN_R	14	13	I	Negative input, right channel
Thermal Pad	n/a	Thermal Pad	Р	Connect to ground

(1) I = input, O = output, P = power



SYSTEM BLOCK DIAGRAM



ORDERING INFORMATION(1)

T _A	PACKAGE	DESCRIPTION		
40°C to 95°C	DRV612PW	14-pin TSSOP		
–40°C to 85°C	DRV612RGT	16-pin QFN		

⁽¹⁾ For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI Web site at www.ti.com.

THERMAL INFORMATION

	THERMAL METRIC ⁽¹⁾	DRV612	DRV612	LIMITO
	THERMAL METRIC	RGT (16-Pin)	PW (14-Pin)	UNITS
θ_{JA}	Junction-to-ambient thermal resistance	52	130	
θ_{JCtop}	Junction-to-case (top) thermal resistance	71	49	
θ_{JB}	Junction-to-board thermal resistance	26	63	°C/W
ΨЈТ	Junction-to-top characterization parameter	3.0	3.6	C/VV
ΨЈВ	Junction-to-board characterization parameter	26	62	
θ_{JCbot}	Junction-to-case (bottom) thermal resistance	n/a	n/a	

(1) For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.



ABSOLUTE MAXIMUM RATINGS(1)

over operating free-air temperature range (unless otherwise noted)

			VAI	MIN MAX -0.3 4 VSS - 0.3 VDD + 0.3 -0.3 VDD + 0.3		
			MIN	MAX		
	VDD to GND		-0.3	4		
Voltage range	V _I , Input volta	age	VSS - 0.3	VDD + 0.3	V	
	MUTE to GNI	MUTE to GND -0.3 VDD + 0	VDD + 0.3	1		
T	Maximum ope	erating junction temperature range, T _J	-40	150	00	
Temperature	Storage temp	erature	-65	4 VDD + 0.3 VDD + 0.3	-0	
Electrostatic discharge (HBM) QSS 009-105 (JESD22-A114A)		OUT_L, OUT_R	8	3	1.1/	
		All other pins		2		

⁽¹⁾ Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

RECOMMENDED OPERATING CONDITIONS

over operating free-air temperature range unless otherwise noted

			MIN	NOM	MAX	UNIT
VDD	Supply voltage	DC supply voltage	3.0	3.3	3.6	V
R _L			600	10k		Ω
V _{IL}	Low-level input voltage	MUTE	38	40	43	%VDD
V _{IH}	High-level input voltage	MUTE	57	60	66	%VDD
T _A	Free-air temperature		-0	25	85	°C



ELECTRICAL CHARACTERISTICS

VDD = 3.3V, R_{LD} = 5 k Ω , T_A = 25°C, Charge pump: C_{CP} = 1 μF , unless otherwise noted.

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
V _{OS}	Output offset voltage	VDD = 3.3 V, input ac-coupled		0.5	1	mV
PSRR	Power-supply rejection ratio		70	80		dB
V _{OH}	High-level output voltage	VDD = 3.3 V	3.1			V
V _{OL}	Low-level output voltage	VDD = 3.3 V			-3.05	V
Vuvp_on	VDD, undervoltage detection				2.8	V
Vuvp_hysteresis	VDD, undervoltage detection, hysteresis			200		mV
F _{CP}	Charge-pump switching frequency			350		kHz
[Іін]	High-level input current, MUTE	VDD = 3.3 V, V _{IH} = VDD			1	μA
I _{IL}	Low-level input current, MUTE	VDD = 3.3 V, V _{IL} = 0 V			1	μA
I _(VDD)	Supply current, no load	VDD, MUTE = 3.3 V		18		mA
	Supply current, MUTED	VDD = 3.3 V, MUTE = GND		18		mA
T _{SD}	Thermal shutdown			150		°C
	Thermal shutdown hysteresis			15		°C

ELECTRICAL CHARACTERISTICS, LINE DRIVER

VDD = 3.3 V, $R_{I,OAD}$ = 10 k Ω , T_A = 25°C, Charge pump: C_{CP} = 1 μ F, 1× gain select (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
Vo	Output voltage, outputs in phase	1% THD+N, f = 1 kHz, 10 -kΩ load	2.2		V_{rms}
THD+N	Total harmonic distortion plus noise	$f = 1 \text{ kHz}$, 10-k Ω load, $V_O = 2 V_{rms}$	0.007%		
SNR	Signal-to-noise ratio	A-weighted, AES17 filter, 2 V _{rms} ref	105		dB
DNR	Dynamic range	A-weighted, AES17 filter, 2 V _{rms} ref	105		dB
Vn	Noise voltage	A-weighted, AES17 filter	12		μV
Zo	Output impedance when muted	MUTE = GND	0.07	1	Ω
	Input-to-output attenuation when muted	1 Vrms, 1-kHz input	80		dB
	Slew rate		4.5		V/µs
G _{BW}	Unity-gain bandwidth		8		MHz
	Crosstalk – Line L-R and R-L	10-kΩ load, V _O = 2 Vrms	-91		dB
I _{limit}	Current limit	VDD = 3.3 V	25		mA



PROGRAMMABLE GAIN SETTINGS(1)(2)

VDD = 3.3 V, R_{load} = 10 k Ω , T_A = 25°C, Charge pump: C_{CP} = 1 μ F, 1× gain select, unless otherwise noted

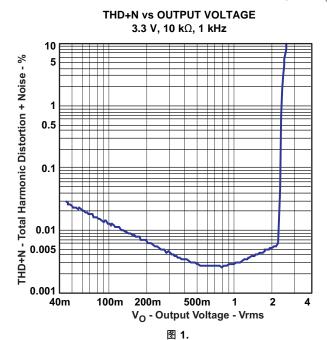
	PARAMETER	TEST CONDITIONS	MIN TY	P MAX	UNIT
R_Tol	Gain programming resistor tolerance			2%	
ΔA_{V}	Gain matching	Between left and right channels	0.2	25	dB
	Gain step tolerance		0	.1	dB
	Gain steps	Gain resistor 2% tolerance 249k or higher 82k5 51k1 34k8 27k4 20k5 15k4 11k5 9k09 7k50 6k19 5k11 4k22	-1 -1 -2 -2 -3 -3	.3 .5 .3 .5 .4 -4 -6 .6 .4 .3	V/V
	Input impedance	Gain resistor 2% tolerance 249k or higher 82k5 51k1 34k8 27k4 20k5 15k4 11k5 9k09 7k50 6k19 5k11 4k22		37 55 44 33 31 28 24 22 18 17 15	kΩ

⁽¹⁾ If the GAIN pin is left floating, an internal pullup sets the gain to -2×.
(2) Gain setting is latched during power up.

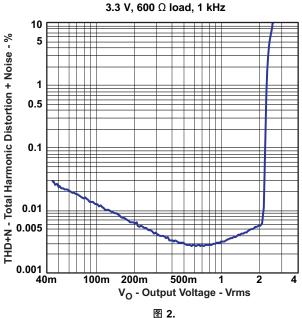


TYPICAL CHARACTERISTICS, LINE DRIVER

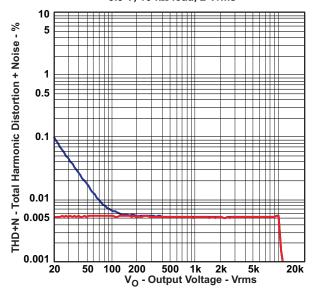
 V_{DD} = 3.3 V, T_A = 25°C, R_L = 2.5 k Ω , C_{PUMP} = $C_{(VSS)}$ = 1 μ F, Gain = -2V/V (unless otherwise noted)



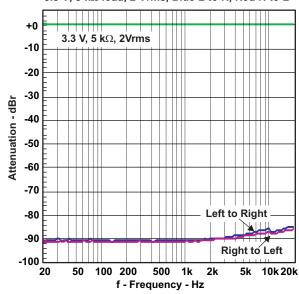
THD+N vs OUTPUT VOLTAGE



THD+N vs FREQUENCY 3.3 V, 10 k Ω load, 2 Vrms



CHANNEL SEPARATION 3.3 V, 5 k Ω load, 2 Vrms, Blue L to R, Red R to L



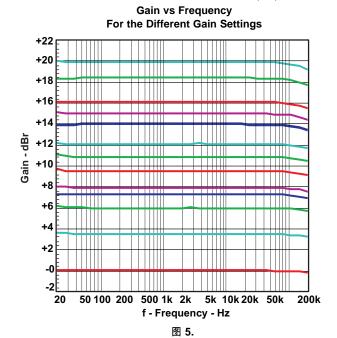
Blue: 10-µF ceramic ac-coupling capacitor.
Red: 10-µF electrolytic ac-coupling capacitor
图 3.

图 4.



TYPICAL CHARACTERISTICS, LINE DRIVER (接下页)

 V_{DD} = 3.3 V, T_A = 25°C, R_L = 2.5 k Ω , C_{PUMP} = $C_{(VSS)}$ = 1 μ F, Gain = -2V/V (unless otherwise noted)



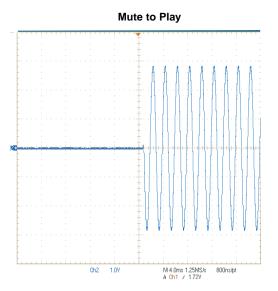
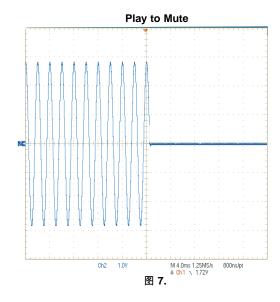


图 6.





APPLICATION INFORMATION

LINE DRIVER AMPLIFIERS

Single-supply line-driver amplifiers typically require dc-blocking capacitors. The top drawing in 8 8 illustrates the conventional line-driver amplifier connection to the load and output signal.

DC blocking capacitors are often large in value, and a mute circuit is needed during power up to minimize click and pop. The output capacitor and mute circuit consume PCB area and increase cost of assembly, and can reduce the fidelity of the audio output signal.

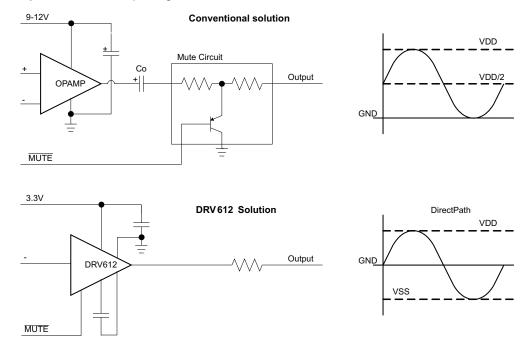


图 8. Conventional and DirectPath Line Driver

The DirectPath amplifier architecture operates from a single supply but makes use of an internal charge pump to provide a negative voltage rail.

Combining the user-provided positive rail and the negative rail generated by the IC, the device operates in what is effectively a split supply mode.

The output voltages are now centered at zero volts with the capability to swing to the positive rail or negative rail. Combining this with the built-in click- and pop-reduction circuit, the DirectPath amplifier requires no output dc-blocking capacitors.

The bottom block diagram and waveform of 8 8 illustrate the ground-referenced line-driver architecture. This is the architecture of the DRV612.



COMPONENT SELECTION

Charge Pump Flying Capacitor and VSS Capacitor

The charge-pump flying capacitor serves to transfer charge during the generation of the negative supply voltage. The VSS capacitor must be at least equal to the charge pump capacitor in order to allow maximum charge transfer. Low-ESR capacitors are an ideal selection, and a value of 1 µF is typical.

Decoupling Capacitors

The DRV612 is a DirectPath line-driver amplifier that requires adequate power-supply decoupling to ensure that the noise and total harmonic distortion (THD) are low. A good low equivalent-series-resistance (ESR) ceramic capacitor, typically 1 μ F, placed as close as possible to the device VDD lead works best. Placing this decoupling capacitor close to the DRV612 is important for the performance of the amplifier. For filtering lower-frequency noise signals, a 10- μ F or greater capacitor placed near the audio power amplifier also helps, but it is not required in most applications because of the high PSRR of this device.

Gain-Setting

The gain setting is programmed with the GAIN pin. Gain setting is latched durning power on. 表 1 lists the gain settings.

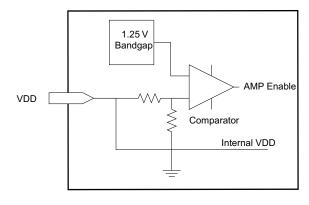
NOTE: If gain pin is left unconnected (open) default gain of -2× is selected.

		•	
Gain_set RESISTOR	GAIN	GAIN (dB)	INPUT RESISTANCE
249 kΩ ⁽¹⁾	–2×	6	37 kΩ
82k5	–1×	0.0	55 kΩ
51k1	−1.5×	3.5	44 kΩ
34k8	-2.3×	7.2	33 kΩ
27k4	-2.5×	8	31 kΩ
20k5	_3×	9.5	28 kΩ
15k4	-3.5×	10.9	24 kΩ
11k5	-4.0×	12	22 kΩ
9k09	_5×	14	18 kΩ
7k5	-5.6×	15	17 kΩ
6k19	-6.4×	16.1	15 kΩ
5k11	-8.3×	18.4	12 kΩ
4k22	–10×	20	10 kΩ

表 1. Gain Settings

Internal Undervoltage Detection

The DRV612 contains an internal precision band-gap reference voltage and a comparator used to monitor the supply voltage, VDD. The internal VDD monitor is set at 2.8 V with 200-mV hysteresis.



⁽¹⁾ or higher



Input-Blocking Capacitors

DC input-blocking capacitors are required to be added in series with the audio signal into the input pins of the DRV612. These capacitors block the dc portion of the audio source and allow the DRV612 inputs to be properly biased to provide maximum performance. The input blocking capacitors also limit the dc gain to 1, limiting the dc-offset voltage at the output.

These capacitors form a high-pass filter with the input resistor, R_{IN} . The cutoff frequency is calculated using Δ 1. For this calculation, the capacitance used is the input-blocking capacitor and the resistance is the input resistor chosen from \pm 2. Then the frequency and/or capacitance can be determined when one of the two values is given.

$$fc_{IN} = \frac{1}{2\pi R_{IN} C_{IN}}$$
 or $C_{IN} = \frac{1}{2\pi fc_{IN} R_{IN}}$ (1)

For a fixed cutoff frequency of 2 Hz, the size of the input capacitance is shown in 表 2 with the capacitors rounded up to nearest E6 values. For 20-Hz cutoff, simply divide the capacitor values with 10; e.g., for 1× gain, 150 nF is needed.

Z = mput supusion is zmooth sum and suite									
Gain_set RESISTOR	GAIN	Gain (dB)	INPUT RESISTANCE	2 Hz Cutoff					
249 kΩ	–2 ×	6	37 kΩ	2.2 µF					
82k5	−1 ×	0.0	55 kΩ	1.5 µF					
51k1	-1.5×	3.5	44 kΩ	2.2 µF					
34k8	-2.3×	7.2	33 kΩ	3.3 µF					
27k4	-2.5×	8	31 kΩ	3.3 µF					
20k5	-3×	9.5	28 kΩ	3.3 µF					
15k4	-3.5×	10.9	24 kΩ	3.3 µF					
11k5	_4×	12	22 kΩ	4.7 µF					
9k09	–5×	14	18 kΩ	4.7 µF					
7k5	-5.6×	15	17 kΩ	4.7 µF					
6k19	-6.4×	16.1	15 kΩ	6.8 µF					
5k11	-8.3×	18.4	12 kΩ	6.8 µF					
4k22	-10×	20	10 kΩ	10 μF					

表 2. Input Capacitor for Different Gain and Cutoff

Pop-Free Power Up

Pop-free power up is ensured by keeping the MUTE pin low during power-supply ramp-up and -down. The pins should be kept low until the input ac-coupling capacitors are fully charged before asserting the MUTE pin high, this way proper pre-charge of the ac-coupling is performed and pop-less power up is achieved. 图 9 illustrates the preferred sequence.

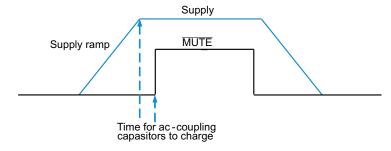


图 9. Power-Up/Down Sequence



CAPACITIVE LOAD

The DRV612 has the ability to drive a high capacitive load up to 220 pF directly. Higher capacitive loads can be accepted by adding a series resistor of 47 Ω or larger for the line driver output.

LAYOUT RECOMMENDATIONS

A proposed layout for the DRV612 can be seen in the DRV612EVM User's Guide (SLOU248), and the Gerber files can be downloaded from http://focus.ti.com/docs/toolsw/folders/print/DRV612evm.html. To access this information, open the DRV612 product folder and look in the Tools and Software folder.

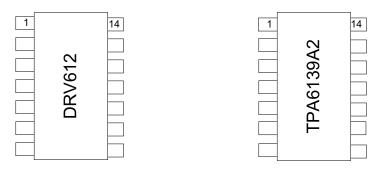
Ground traces are recommended to be routed as a star ground to minimize hum interference. VDD, VSS decoupling capacitors and the charge-pump capacitors should be connected with short traces.

12



FOOTPRINT COMPATIBLE WITH TPA6139A2

The DRV612 stereo line driver is pin compatible with the headphone amplifier TPA6139A2. Therefore, a single PCB layout can be used with stuffing options for different board configurations.



APPLICATION CIRCUIT

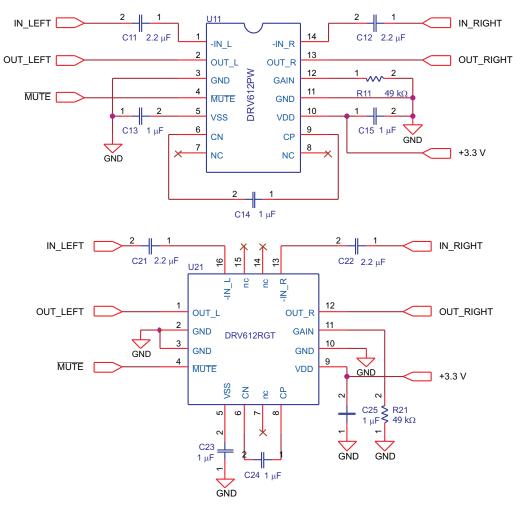


图 10. Single-Ended Input and Output, Gain Set to -1.5×



REVISION HISTORY

Cł	nanges from Original (December 2010) to Revision A	Page
•	Added the QFN pinout drawing	2
•	Added the QFN device To the PIN FUNCTIONS table	2
•	Changed the Abs Max Storage Temp From: MIN = -40 To: MIN = -65	4
•	Changed the Gain resistor 2% tolerance values in the Programmable Gain Settings table For Gain Steps and Input Impedance	
•	Changed Note 1 of the PROGRAMMABLE GAIN SETTINGS table From: If pin 12, GAIN, is left floating To: If the GAIN pin is left floating	6
•	Changed From: $C_{PUMP} = C_{(VSS)} = 10 \ \mu F$ To: $C_{PUMP} = C_{(VSS)} = 1 \ \mu F$ in the Typical Characteristics condition text	7
•	Changed the Gain_set RESISTOR values in 表 1	10
•	Changed the Gain_set RESISTOR values in 表 2	11
•	Removed references to DRV614 from the FOOTPRINT COMPATIBLE WITH TPA6139A2 secton	13
Cł	nanges from Revision A (February 2011) to Revision B	Page
•	Deleted the Product Preview note from the RGT package	3
•	Changed $R_{IN} = 10 \text{ k}\Omega$, $R_{fb} = 20 \text{ k}\Omega$ To Gain = -2V/V in the Typical Characteristics condition text	7

产品主页链接:DRV612





11-Dec-2020

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
DRV612PW	ACTIVE	TSSOP	PW	14	90	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	DRV612	Samples
DRV612PWR	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	DRV612	Samples
DRV612RGTR	ACTIVE	VQFN	RGT	16	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	D612	Samples
DRV612RGTT	ACTIVE	VQFN	RGT	16	250	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	D612	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS**: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

11-Dec-2020

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PACKAGE MATERIALS INFORMATION

www.ti.com 5-Dec-2023

TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

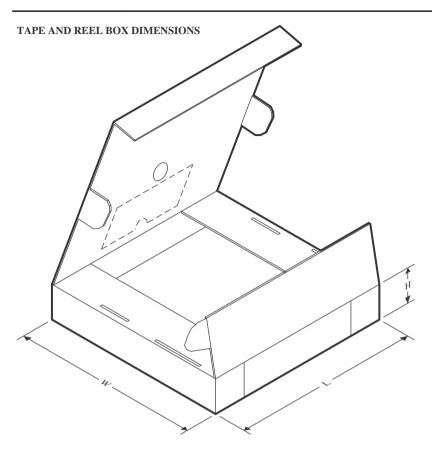
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
DRV612PWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
DRV612RGTR	VQFN	RGT	16	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
DRV612RGTT	VQFN	RGT	16	250	180.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2

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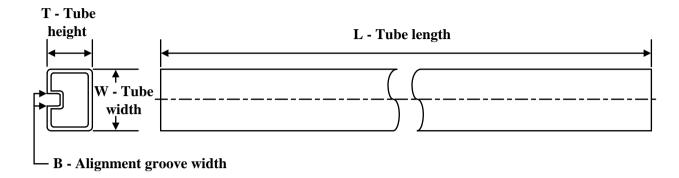
*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
DRV612PWR	TSSOP	PW	14	2000	350.0	350.0	43.0
DRV612RGTR	VQFN	RGT	16	3000	346.0	346.0	33.0
DRV612RGTT	VQFN	RGT	16	250	210.0	185.0	35.0

PACKAGE MATERIALS INFORMATION

www.ti.com 5-Dec-2023

TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
DRV612PW	PW	TSSOP	14	90	530	10.2	3600	3.5

PW (R-PDSO-G14)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
- E. Falls within JEDEC MO-153



PW (R-PDSO-G14)

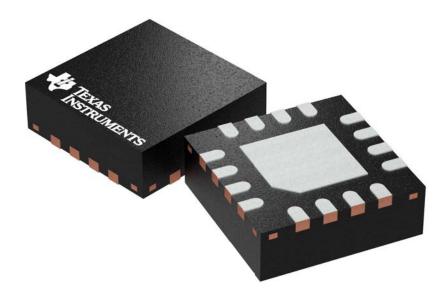
PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.





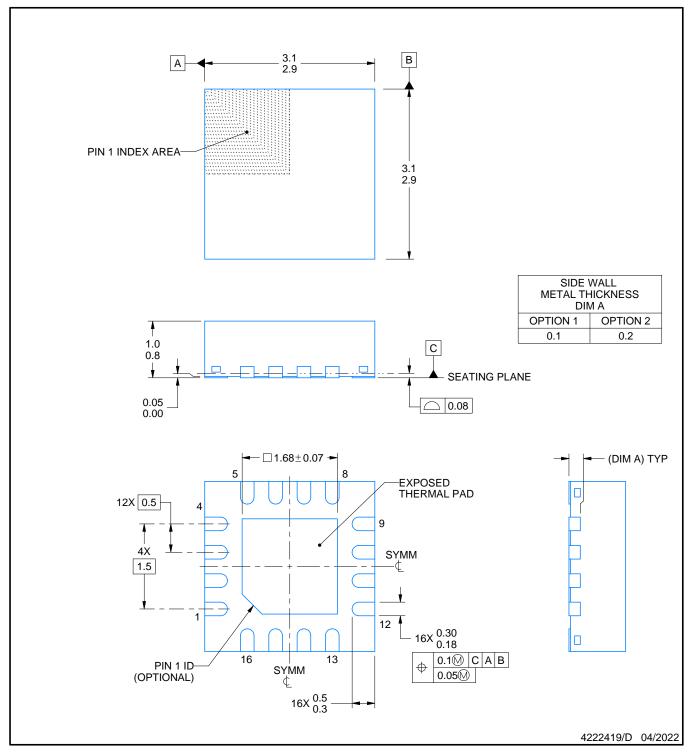
Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.







PLASTIC QUAD FLATPACK - NO LEAD

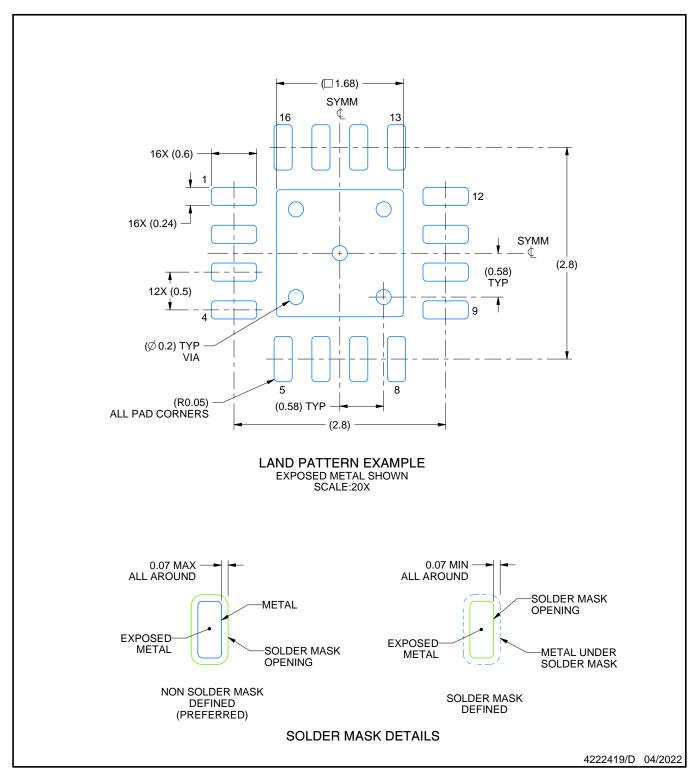


NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.



PLASTIC QUAD FLATPACK - NO LEAD

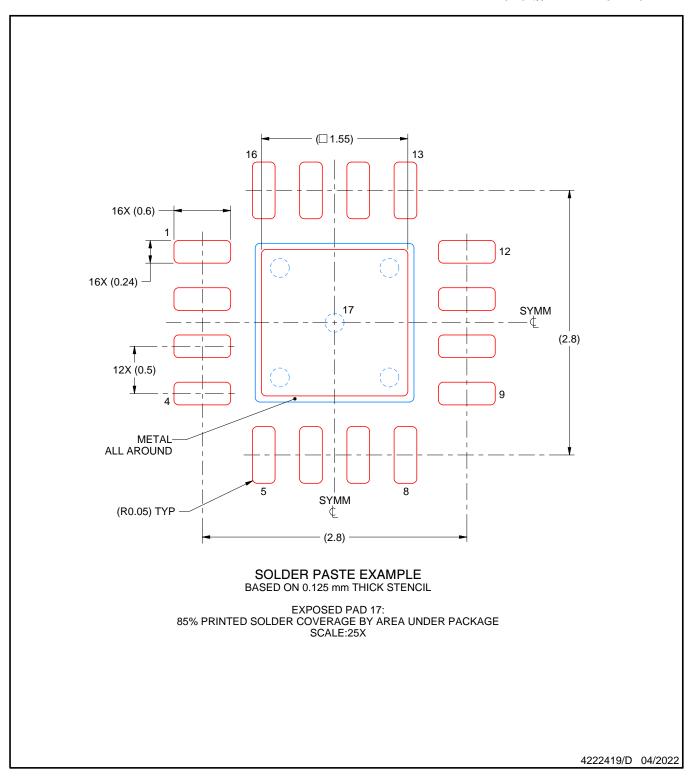


NOTES: (continued)

- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



PLASTIC QUAD FLATPACK - NO LEAD



NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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